

FIG. 1

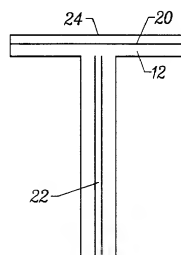


FIG. 2

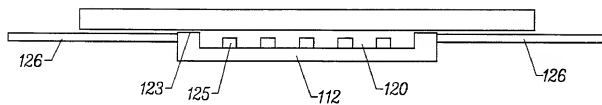


FIG. 3A

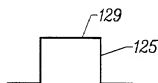
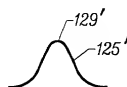
FIG. 3B  
(Prior Art)

FIG. 3C

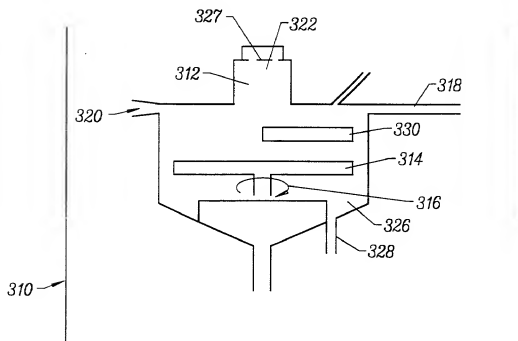


FIG. 5

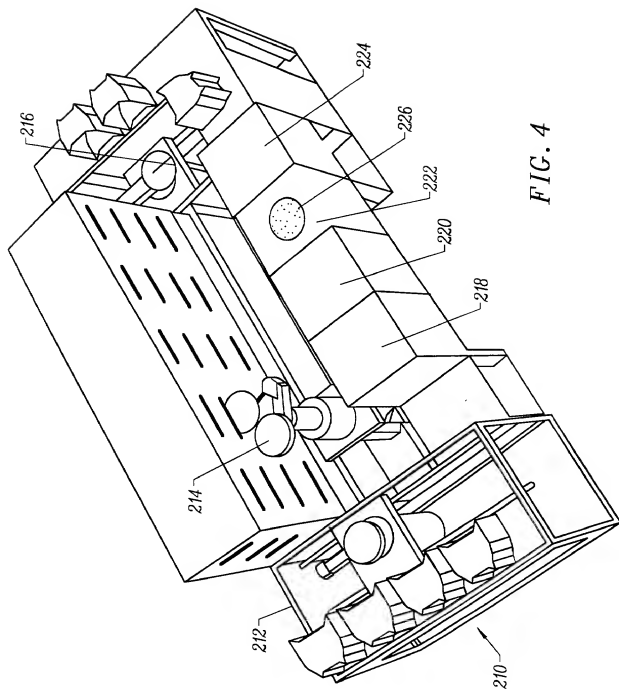


FIG. 4

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Developer Chuck Surface Treatment Comparison: Backside Contamination  
over  $0.3\mu\text{m}$  after 1 hour ultrasonic IPA

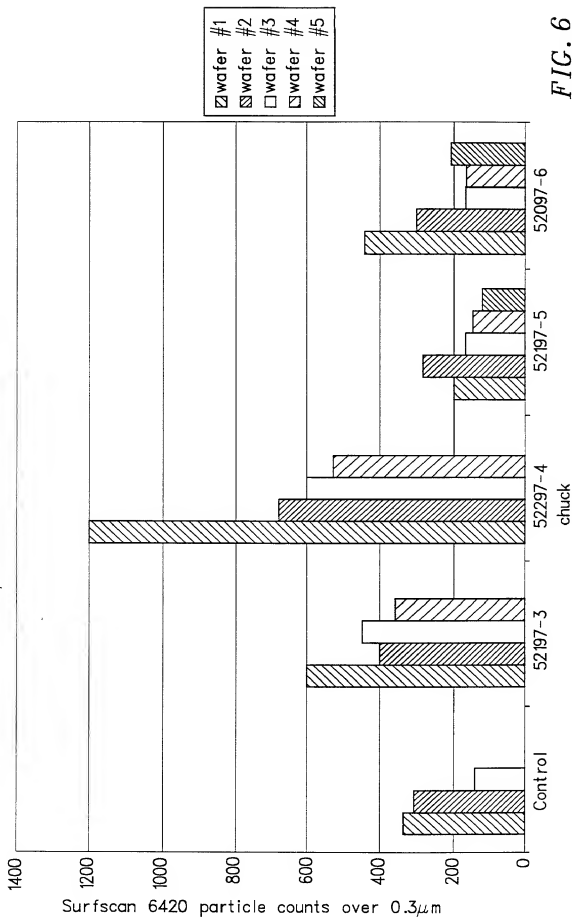


FIG. 6

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# Minimization of Surface Contact Area

Coating uniformity is not compromised when the wafer-to-chuck contact "dimples" are reduced by 50%.

Coat Parameter	Std Chuck	Reduced Dimple Chuck
X-Wafer Uniformity	7.5	6
W-W Uniformity	3.89	1.84

Coating Uniformity: Std Chuck vs Reduced Dimple Chuck

□ X-Wafer Uniformity    ▨ W-W Uniformity

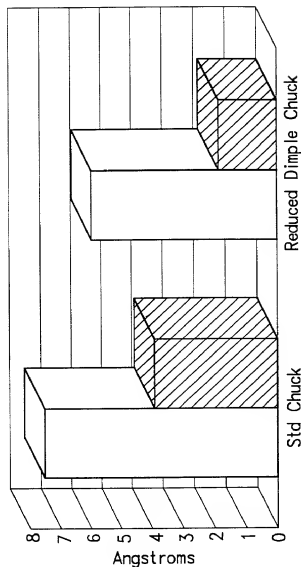


FIG. 7

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# Minimization of Surface Contact Area

Significant reductions in backside contamination is achieved when reducing the number of wafer contact sites.

Wafer #	Std Chuck	Reduced Dimple Chuck	% Reduction
1	13587	7914	41.8
2	8997	5885	34.6
3	6524	5031	22.9

Standard Chuck vs Reduced Dimple Chuck

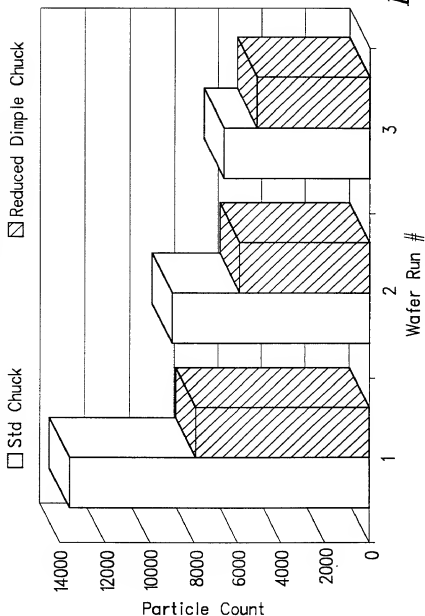


FIG. 8

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